

Marking Information

Site 1



S7 = Product Type Marking Code YM = Date Code Marking Y = Year (ex: H = 2020) M = Month (ex: 9 = September)

Date Code Kev

Date Code Ney												
Year	2016		2020	2021	2022	2023	2024	2025	2026	2027	2028	2029
Code	D		Н		J	K	L	М	N	0	Р	R
	_			-			_			•		
		l.	1	1								
Month	Jan	Feb	Mar	Apr	May	Jun	Jul	Aug	Sep	Oct	Nov	Dec

Site 2



S7 = Product Type Marking Code YWX = Date Code Marking Y = Year (ex: 0 = 2020) W = Week (ex: a = Week 27; z Represents Week 52 and 53) X = Internal Code (ex: U = Monday)

Date Code Key

Year	2016	 2020	2021	2022	2023	2024	2025	2026	2027	2028	2029
Code	6	 0	1	2	3	4	5	6	7	8	9

Week	1-26	27-52	53
Code	A-Z	a-z	z

Internal Code	Sun	Mon	Tue	Wed	Thu	Fri	Sat
Code	Т	U	V	W	X	Y	Z



Maximum Ratings (@TA = +25°C, unless otherwise specified.)

Characteristic		Symbol	Value	Unit	
Drain-Source Voltage		VDSS	30	V	
Gate-Source Voltage	V_{GSS}	±12	V		
Continuous Drain Current (Note 6) V _{GS} = 10V Steady T _A = +25°C State T _A = +70°C			lo	7.0 5.6	А
Maximum Continuous Body Diode Forward Currer	nt (Note 6)		Is	1.5	А
Pulsed Drain Current (10µs Pulse, Duty Cycle = 1	%)	IDM	35	Α	
Avalanche Current (L = 0.1mH) (Note 7)		las	13	Α	
Avalanche Energy (L = 0.1mH) (Note 7)	•		Eas	9	mJ

Thermal Characteristics (@TA = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit		
Total Power Dissipation (Note 5)	T _A = +25°C	PD	0.7	W	
Thermal Resistance, Junction to Ambient (Note 5)	Steady State	D	177	°C/W	
Thermal Resistance, Junction to Ambient (Note 3)	t<10s	RθJA	124	C/VV	
Total Power Dissipation (Note 6)	$T_A = +25^{\circ}C$	P_{D}	2.1	W	
Thermal Resistance, Junction to Ambient (Note 6)	Steady State	р	61	°C/W	
mermal Resistance, Junction to Ambient (Note 6)	t<10s	$R_{\theta JA}$	43	C/VV	
Thermal Resistance, Junction to Case	Steady State	$R_{\theta JC}$	9.3	°C/W	
Operating and Storage Temperature Range		T _{J,} T _{STG}	-55 to +150	°C	

Electrical Characteristics (@TA = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition
OFF CHARACTERISTICS (Note 8)						
Drain-Source Breakdown Voltage	BVDSS	30	_	_	V	$V_{GS} = 0V, I_{D} = 250\mu A$
Zero Gate Voltage Drain Current	I _{DSS}	_	_	1	μΑ	$V_{DS} = 30V, V_{GS} = 0V$
Gate-Source Leakage	Igss		_	±100	nA	$V_{GS} = \pm 12V$, $V_{DS} = 0V$
ON CHARACTERISTICS (Note 8)						
Gate Threshold Voltage	V _{GS(TH)}	0.6	_	1.4	V	$V_{DS} = V_{GS}$, $I_D = 250\mu A$
		_	17	28		$V_{GS} = 10V, I_{D} = 4.0A$
Static Drain-Source On-Resistance	Process		20	32	mΩ	$V_{GS} = 4.5V, I_D = 4.0A$
Static Dialii-Source Off-Resistance	RDS(ON)	l	24	42	11152	$V_{GS} = 3.0V, I_{D} = 4.0A$
		l	28	50		$V_{GS} = 2.5V, I_{D} = 4.0A$
Diode Forward Voltage	V_{SD}		0.7	1.2	V	$V_{GS} = 0V$, $I_S = 1A$
DYNAMIC CHARACTERISTICS (Note 9)						
Input Capacitance	Ciss	_	570	_		15)()(
Output Capacitance	Coss		63	_	pF	V _{DS} = 15V, V _{GS} = 0V f = 1.0MHz
Reverse Transfer Capacitance	Crss	l	53	_		1 = 1.01/11/12
Gate Resistance	R_g	l	3.2	_	Ω	$V_{DS} = 0V$, $V_{GS} = 0V$, $f = 1.0MHz$
Total Gate Charge (V _{GS} = 10V)	Qg	_	13.3	_		
Total Gate Charge (V _{GS} = 4.5V)	Qg	_	6.1	_	nC	V _{DS} = 15V, I _D = 6.9A
Gate-Source Charge	Qgs	_	1.0	_	IIC	VDS = 15V, ID = 6.9A
Gate-Drain Charge	Q_{gd}		1.6	_		
Turn-On Delay Time	t _{D(ON)}	_	1.5	_		
Turn-On Rise Time	t _R	_	3.3	_		$V_{GS} = 10V, V_{DD} = 15V, R_g = 3\Omega,$
Turn-Off Delay Time	t _{D(OFF)}	_	13.9	_	ns	I _D = 6.9A
Turn-Off Fall Time	tF	_	4.9	_		
Body Diode Reverse Recovery Time	trr	_	7.8	_	ns	Is = 5A, dI/dt = 100A/µs
Body Diode Reverse Recovery Charge	Qrr	_	1.9	_	nC	Is = 5A, dI/dt = 100A/µs

Notes: 5. Device mounted on FR-4 substrate PC board, 2oz copper, with minimum recommended pad layout.

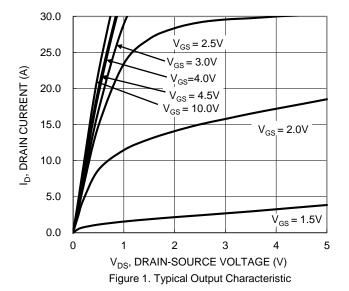
^{6.} Device mounted on FR-4 substrate PC board, 2oz copper, with 1inch square copper plate.

^{7.} I_{AS} and E_{AS} ratings are based on low frequency and duty cycles to keep T_J = +25°C.

^{8.} Short duration pulse test used to minimize self-heating effect.

^{9.} Guaranteed by design. Not subject to product testing.





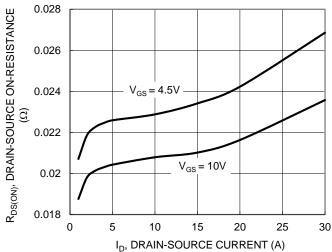


Figure 3. Typical On-Resistance vs. Drain Current and Gate Voltage

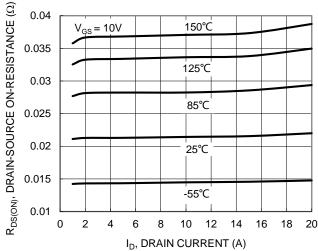


Figure 5. Typical On-Resistance vs. Drain Current and Temperature

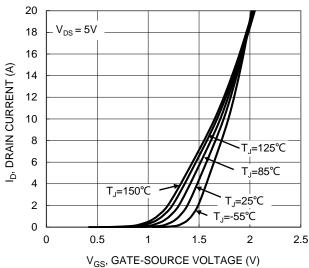


Figure 2. Typical Transfer Characteristic

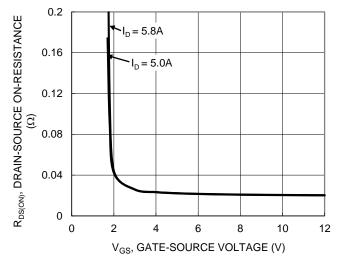


Figure 4. Typical Transfer Characteristic

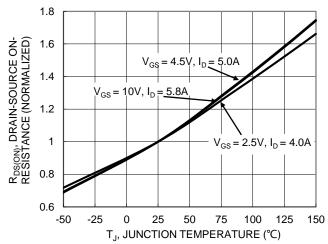


Figure 6. On-Resistance Variation with Temperature



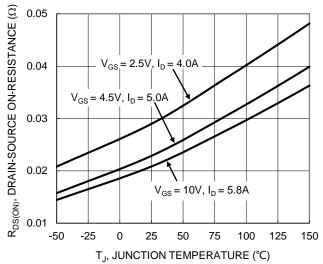


Figure 7. On-Resistance Variation with Temperature

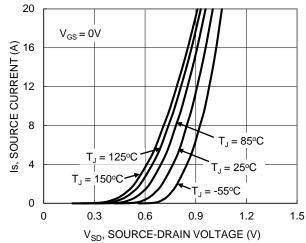
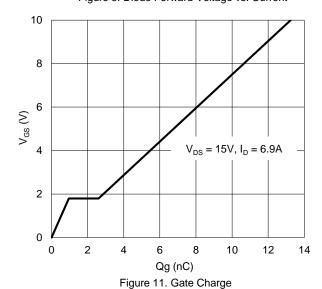


Figure 9. Diode Forward Voltage vs. Current



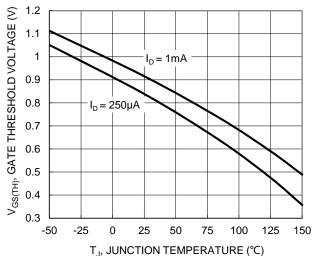


Figure 8. Gate Threshold Variation vs. Junction Temperature

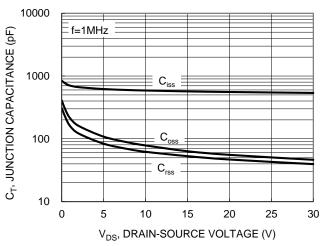
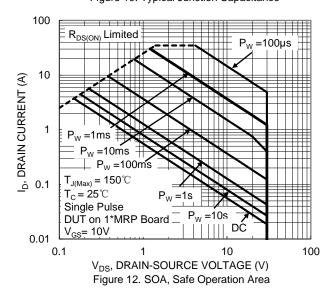


Figure 10. Typical Junction Capacitance





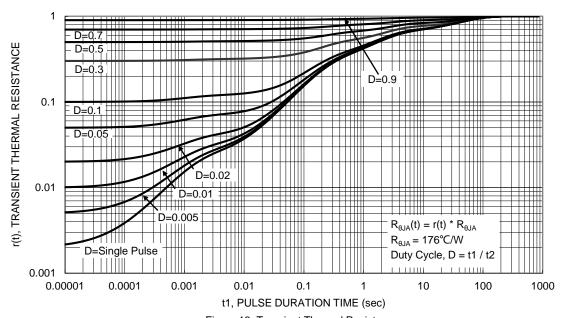


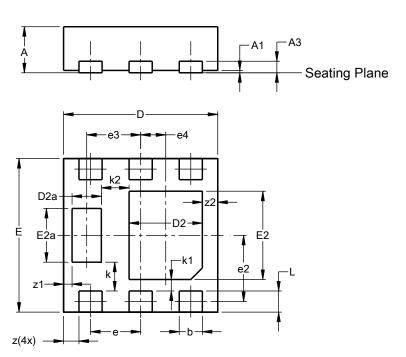
Figure 13. Transient Thermal Resistance



Package Outline Dimensions

Please see http://www.diodes.com/package-outlines.html for the latest version.

U-DFN2020-6 (Type F)

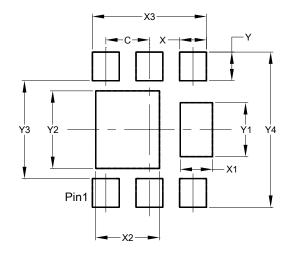


U-DFN2020-6						
	(Тур	oe F)				
Dim	Min					
Α	0.57	0.60				
A1	0.00	0.05	0.03			
A3	-	-	0.15			
b	0.25	0.35	0.30			
D	1.95	2.05	2.00			
D2	0.85	1.05	0.95			
D2a	0.33	0.33 0.43 0.				
Е	1.95	2.05	2.00			
E2	1.05	1.25	1.15			
E2a	0.65	0.75	0.70			
е		0.65 BS	С			
e2	().863 BS	SC			
е3		0.70 BS	С			
e4	().325 BS	SC			
k		0.37 BS				
k1	0.15 BSC					
k2	0.36 BSC					
L	0.225 0.325 0.275					
Z	0.20 BSC					
z 1	0.110 BSC					
z2		0.20 BS	_			
All C	Dimens	ions in	mm			

Suggested Pad Layout

Please see http://www.diodes.com/package-outlines.html for the latest version.

U-DFN2020-6 (Type F)



Dimensions	Value				
	(in mm)				
С	0.650				
X	0.400				
X1	0.480				
X2	0.950				
Х3	1.700				
Y	0.425				
Y1	0.800				
Y2	1.150				
Y3	1.450				
Y4	2.300				



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